

# 2SD1436(K)

Silicon NPN Triple Diffused

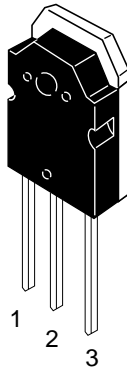
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## Application

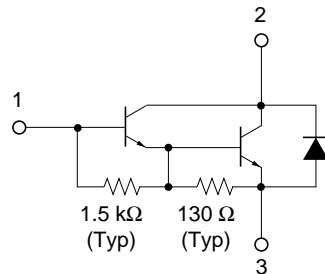
Power switching complementary pair with 2SB1032(K)

## Outline

TO-3P



1. Base
2. Collector (Flange)
3. Emitter



# 2SD1436(K)

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	120	V
Collector to emitter voltage	$V_{CEO}$	120	V
Emitter to base voltage	$V_{EBO}$	7	V
Collector current	$I_C$	10	A
Collector peak current	$I_{C(\text{peak})}$	15	A
Collector power dissipation	$P_C^{*1}$	80	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

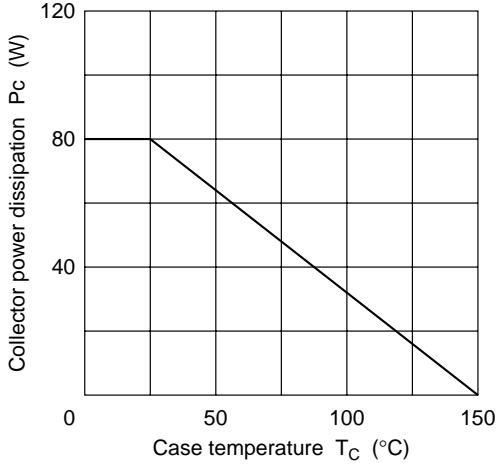
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

## Electrical Characteristics (Ta = 25°C)

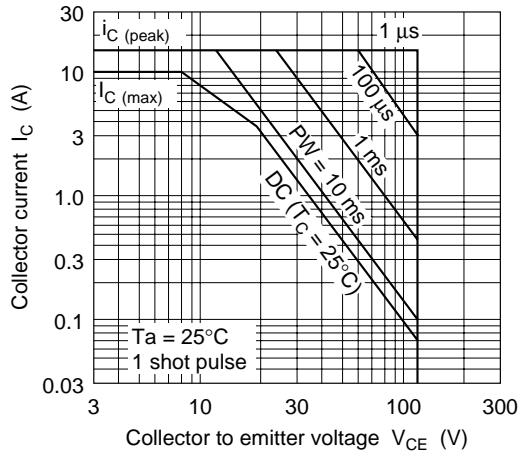
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 25\text{ mA}$ , $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 200\text{ mA}$ , $I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	100	$\mu\text{A}$	$V_{CB} = 120\text{ V}$ , $I_E = 0$
	$I_{CEO}$	—	—	10	$\mu\text{A}$	$V_{CE} = 100\text{ V}$ , $R_{BE} = \infty$
DC current transfer ratio	$h_{FE}$	1000	—	20000		$V_{CE} = 3\text{ V}$ , $I_C = 5\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})1}$	—	—	1.5	V	$I_C = 5\text{ A}$ , $I_B = 10\text{ mA}^{*1}$
	$V_{CE(\text{sat})2}$	—	—	3.0	V	$I_C = 10\text{ A}$ , $I_B = 0.1\text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(\text{sat})1}$	—	—	2.0	V	$I_C = 5\text{ A}$ , $I_B = 10\text{ mA}^{*1}$
	$V_{BE(\text{sat})2}$	—	—	3.5	V	$I_C = 10\text{ A}$ , $I_B = 0.1\text{ A}^{*1}$
Turn on time	Ton	—	0.8	—	$\mu\text{s}$	$I_C = 5\text{ A}$ , $I_{B1} = -I_{B2} = 10\text{ mA}$
Turn off time	Toff	—	4.0	—	$\mu\text{s}$	

Note: 1. Pulse test.

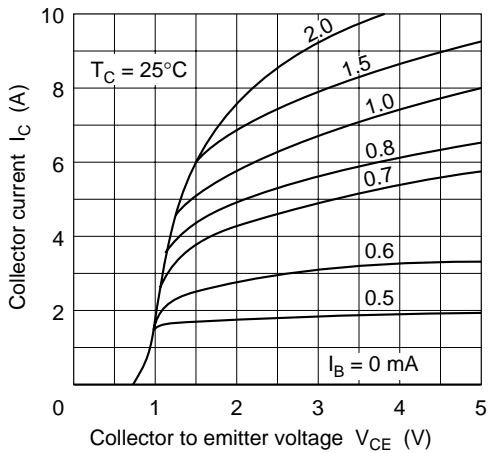
Maximum Collector Dissipation Curve



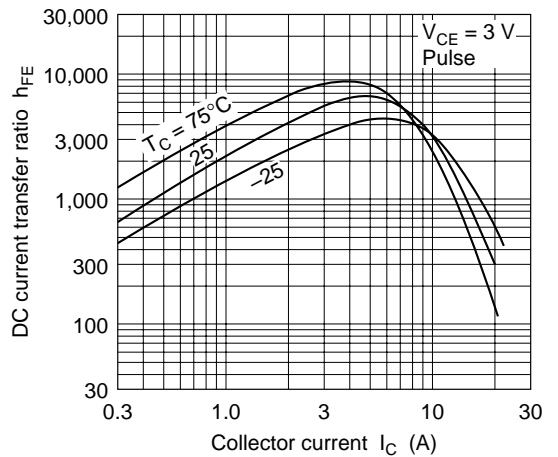
Area of Safe Operation

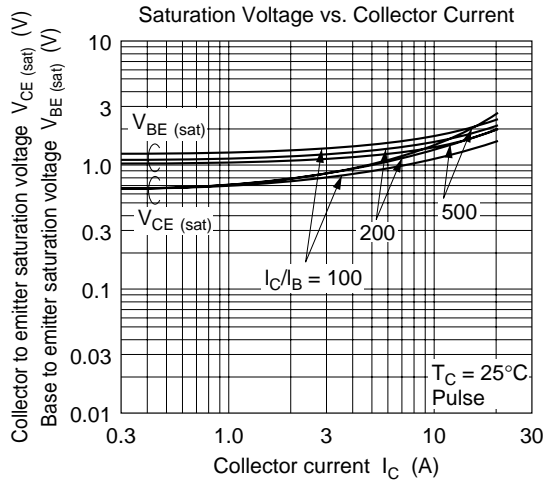


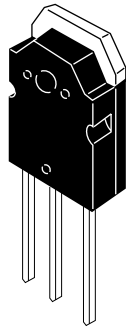
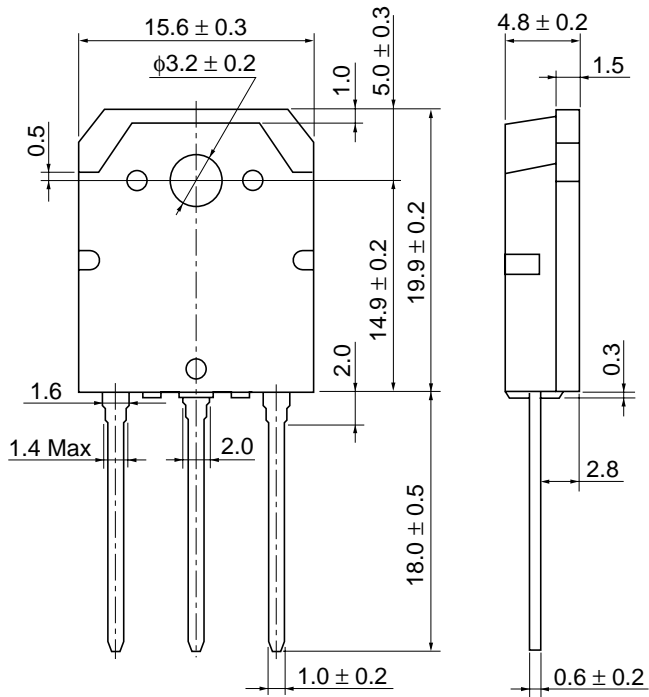
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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